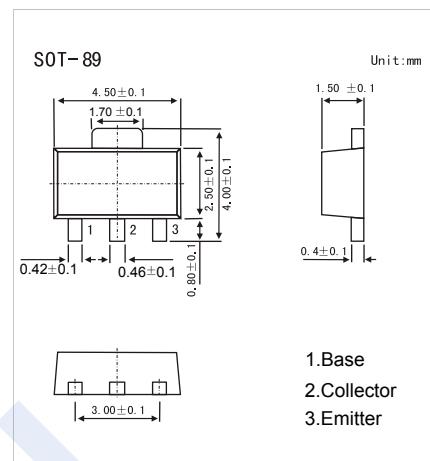


PNP Transistors**2SB1120****■ Features**

- Very small size making it easy to provide high highdensity, small-sized hybrid IC's.
- Low collector-to-emitter saturation voltage
- Large current capacity : $I_C = -2.5A$, $I_{CP} = -5A$.

**■ Absolute Maximum Ratings $T_a = 25^\circ C$**

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-20	V
Collector - Emitter Voltage	V_{CEO}	-10	
Emitter - Base Voltage	V_{EBO}	-7	
Collector Current - Continuous	I_C	-2.5	A
Collector current -Pulse	I_{CP}	-5	
Collector Power Dissipation (Note.1)	P_C	0.5	W
		1.3	
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature range	T_{stg}	-55 to 150	

Note.1: Mounted on ceramic board (250mm² × 0.8mm)

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = -100 \mu A, I_E = 0$	-20			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -1 mA, R_{BE} = \infty$	-10			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -100 \mu A, I_C = 0$	-7			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -16V, I_E = 0$			-0.1	uA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1.5 A, I_B = -150mA$		-0.25	-0.45	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -1.5 A, I_B = -150mA$			-1.2	
DC current gain	h_{FE}	$V_{CE} = -2V, I_C = -500 mA$	100		560	
		$V_{CE} = -2V, I_C = -3 A$	70			
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		70		pF
Transition frequency	f_T	$V_{CE} = -10V, I_C = -50mA$		250		MHz

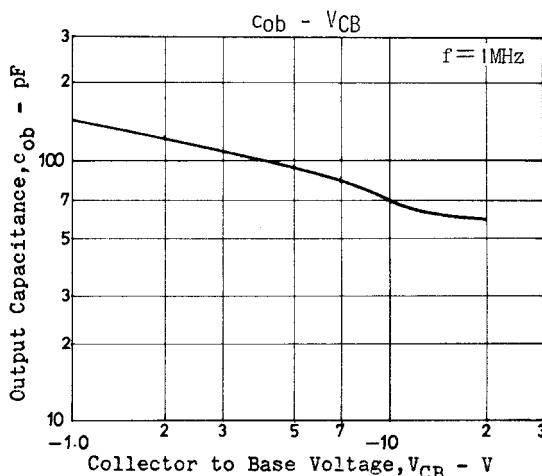
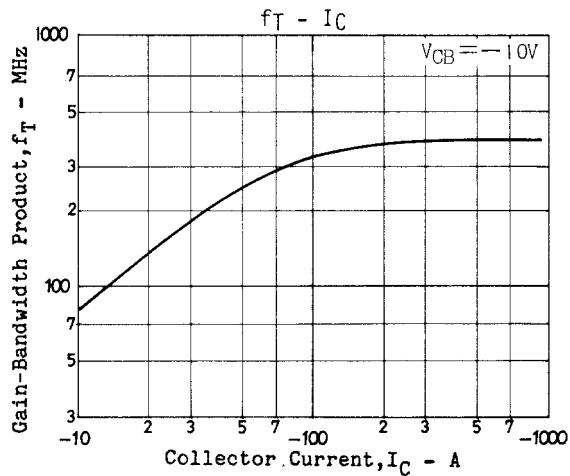
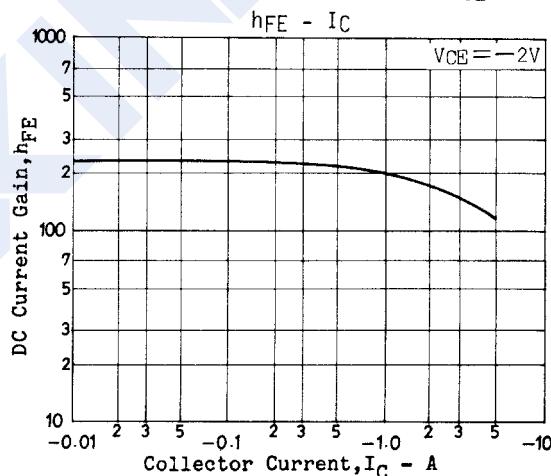
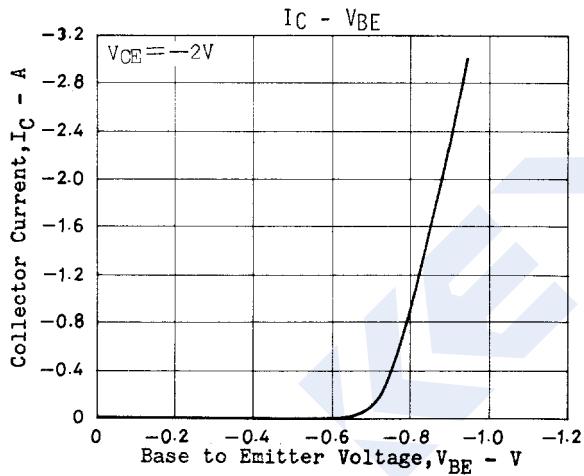
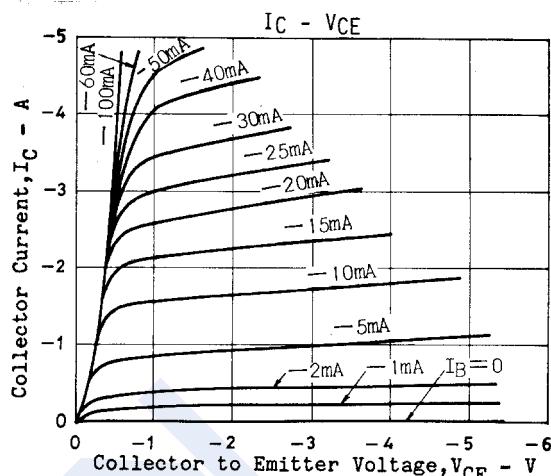
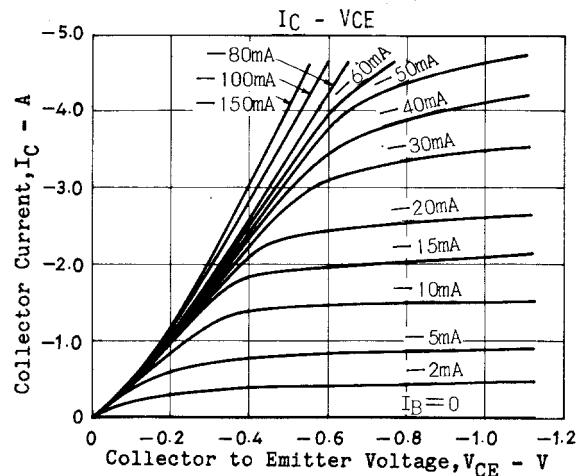
■ Classification of $h_{fe}(1)$

Type	2SB1120-E	2SB1120-F	2SB1120-G
Range	100-200	160-320	280-560
Marking	BC E*	BC F*	BC G*

PNP Transistors

2SB1120

■ Typical Characteristics



PNP Transistors

2SB1120

■ Typical Characteristics

